

FQB12N60C / FQI12N60C

600V N-Channel MOSFET

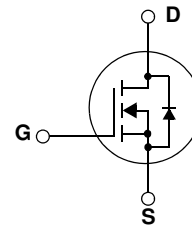
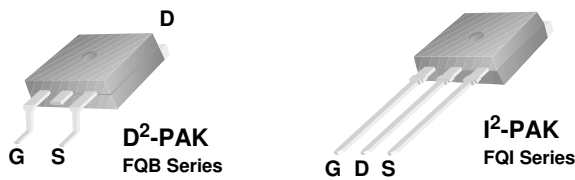
Features

- 12A, 600V, $R_{DS(on)} = 0.65\Omega @ V_{GS} = 10V$
- Low gate charge (typical 48 nC)
- Low Crss (typical 21pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- RoHS compliant

Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficient switched mode power supplies, active power factor correction, electronic lamp ballast based on half bridge topology.



Absolute Maximum Ratings

Symbol	Parameter	FQB12N60C/FQI12N60C	Units
V_{DSS}	Drain-Source Voltage	600	V
I_D	Drain Current	- Continuous ($T_C = 25^\circ\text{C}$)	12
		- Continuous ($T_C = 100^\circ\text{C}$)	7.4
I_{DM}	Drain Current - Pulsed	(Note 1) 48	A
V_{GSS}	Gate-Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy	(Note 2) 870	mJ
I_{AR}	Avalanche Current	(Note 1) 12	A
E_{AR}	Repetitive Avalanche Energy	(Note 1) 22.5	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3) 4.5	V/ns
P_D	Power Dissipation ($T_A = 25^\circ\text{C}$)	3.13	W
	Power Dissipation ($T_C = 25^\circ\text{C}$)	225	W
	- Derate above 25°C	1.78	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8		

Thermal Characteristics

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FQB12N60C	FQB12N60CTM	D2-PAK	330mm	24mm	800
FQI12N60C	FQI12N60CTU	I2-PAK	-	-	50

Electrical Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	600	--	--	V
ΔBV _{DSS} /ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C	--	0.5	--	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 600 V, V _{GS} = 0 V	--	--	1	μA
		V _{DS} = 480 V, T _C = 125°C	--	--	10	μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V	--	--	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V	--	--	-100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	2.0	--	4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 6 A	--	0.53	0.65	Ω
g _{FS}	Forward Transconductance	V _{DS} = 50 V, I _D = 6 A (Note 4)	--	13	--	S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz	--	1760	2290	pF
C _{oss}	Output Capacitance		--	182	235	pF
C _{rss}	Reverse Transfer Capacitance		--	21	28	pF
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} = 300 V, I _D = 12A, R _G = 25 Ω (Note 4, 5)	--	30	70	ns
t _r	Turn-On Rise Time		--	85	180	ns
t _{d(off)}	Turn-Off Delay Time		--	140	280	ns
t _f	Turn-Off Fall Time		--	90	190	ns
Q _g	Total Gate Charge	V _{DS} = 480 V, I _D = 12A, V _{GS} = 10 V (Note 4, 5)	--	48	63	nC
Q _{gs}	Gate-Source Charge		--	8.5	--	nC
Q _{gd}	Gate-Drain Charge		--	21	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	12	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	48	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 12 A	--	--	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 12 A, dI _F / dt = 100 A/μs (Note 4)	--	420	--	ns
Q _{rr}	Reverse Recovery Charge		--	4.9	--	μC

NOTES:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L = 11mH, I_{AS} = 12A, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25°C
3. I_{SD} ≤ 12A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%
5. Essentially independent of operating temperature

Typical Performance Characteristics

Figure 1. On-Region Characteristics

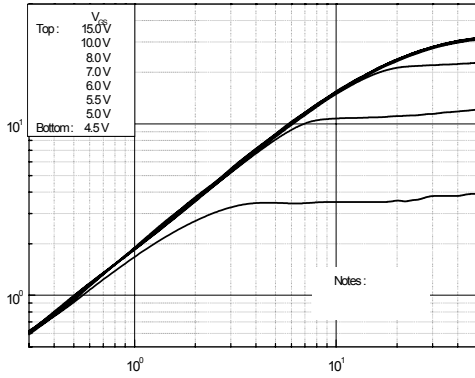


Figure 2. Transfer Characteristics

Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

Figure 5. Capacitance Characteristics

Figure 6. Gate Charge Characteristics

Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

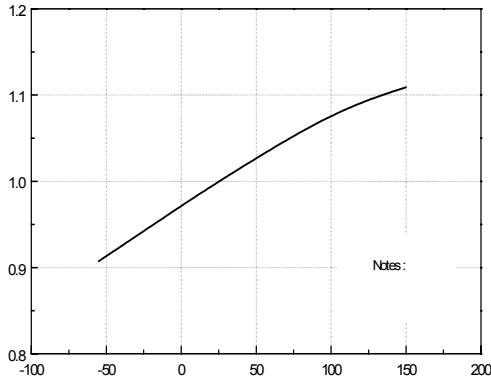


Figure 8. On-Resistance Variation vs. Temperature

Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

Figure 11. Transient Thermal Response Curve

Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

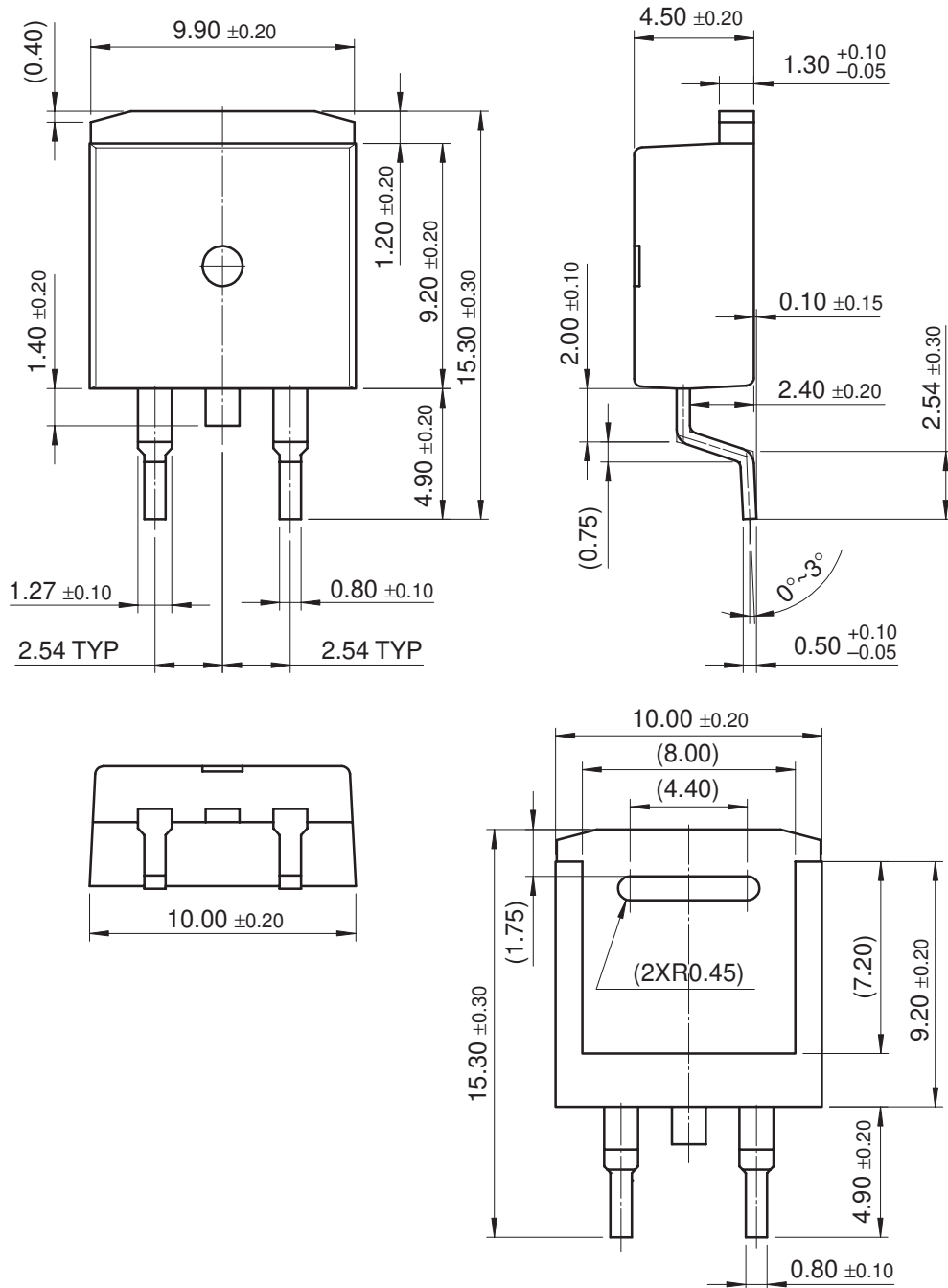


Unclamped Inductive Switching Test Circuit & Waveforms



Package Dimensions

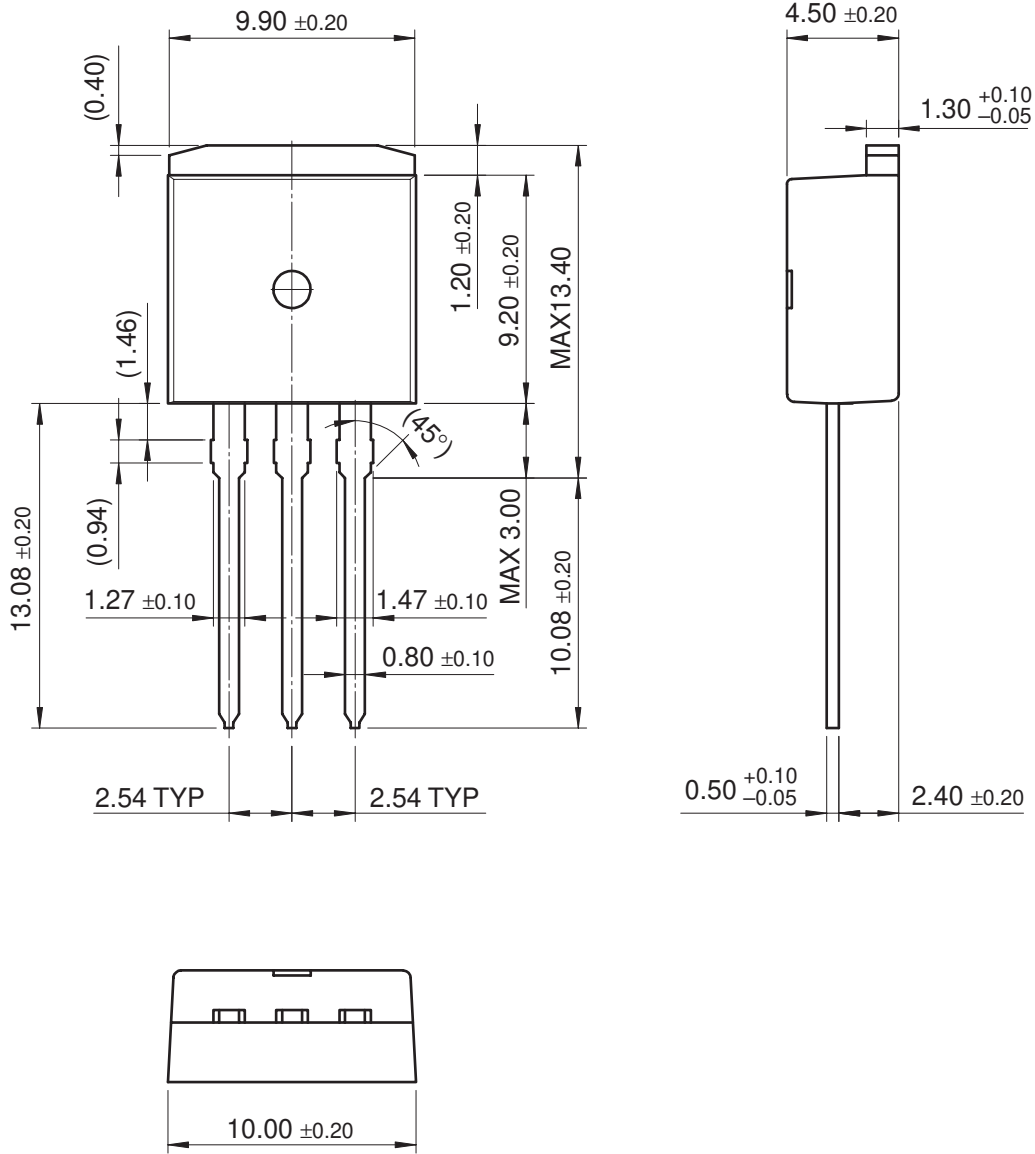
D²-PAK



Dimensions in Millimeters

Package Dimensions (Continued)

I²-PAK




Dimensions in Millimeters



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